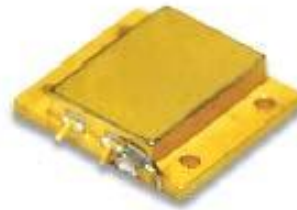


Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 0.5~3.0GHz
- Typical Pout : $\geq 44\text{dBm(CW)}$
- Typical Gain: $\geq 11\text{dB}$
- Typical PAE: $\geq 40\%$
- Bias: 28V/-2~-2.5V@0.5A
- Package: Metal Ceramic

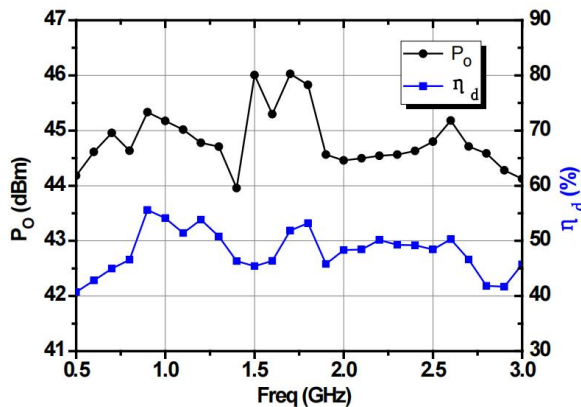


Electrical Specifications (TA=25°C, Vd=28V, Idq=0.5A, F: 0.5~3.0GHz, Pin=33dBm)

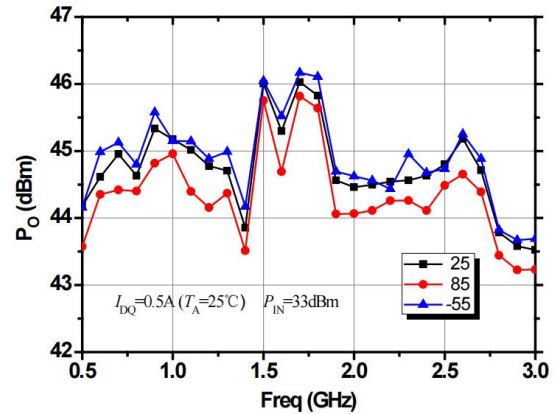
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	44	-	-	dBm
Gp	Power Gain	11	-	-	dB
η_{add}	Power Added Efficiency	40	-	-	%
ΔG_p	Gain Flatness	-	-	± 1.0	dB
Rth	Thermal Resistance	-	2	-	°C/W

Test Curves

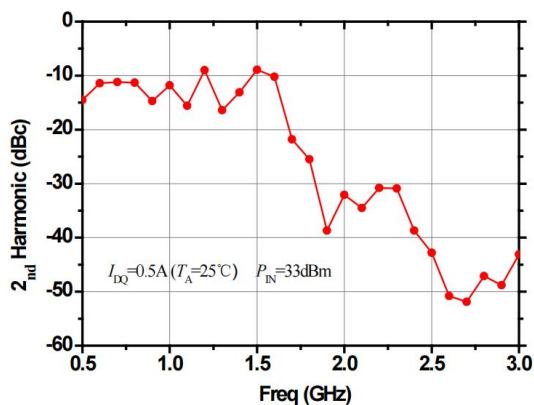
Pout, η_{add} &Freq.



Pout&Freq. @ Different Temp.



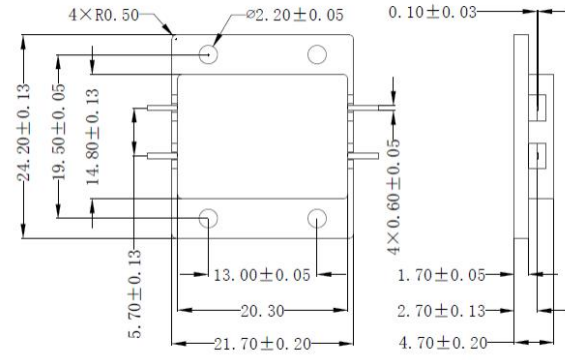
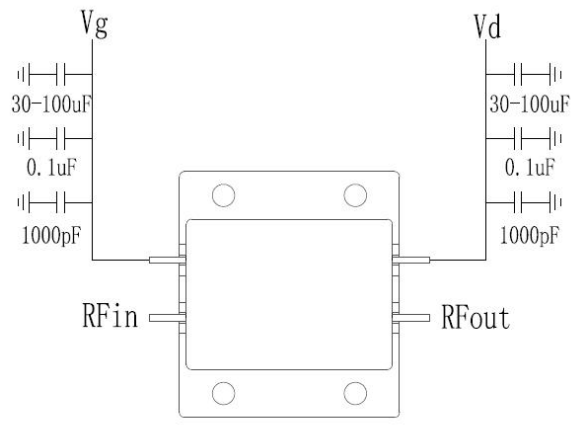
2nd Harmonic&Freq.



Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Voltage	36V	
V _g	Grid Voltage	-5V	
P _d	DC Dissipation	100W	25°C
T _{ch}	Channel Temperature	225°C	【1】
T _m	Mounting Temperature	300°C	1 min, N ₂ Protection
T _{stg}	Storage Temperature	-55~175°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing	Application Circuit
	

Note:

- (1) This product is an internal matching tube, and the input and output impedance values are both 50 ohms;
- (2) Please strictly follow the order of adding negative electricity first and then positive electricity in the power-on sequence. When de-energizing, first reduce the drain voltage and then reduce the gate voltage;
- (3) This product is a high-power device. It is necessary to pay attention to heat dissipation during use. The higher the case temperature, the shorter the service life. It is advisable to use the temperature not higher than 85 degrees;
- (4) This product is an electrostatic sensitive device. It is necessary to pay attention to electrostatic protection during storage and use, and it needs to be well grounded when using it;
- (5) The input standing wave is relatively high, and isolation measures are required at the input end.